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Abstract

Semiconductor component with stress-absorbing semiconductor layer, and associated fabrication method

The invention relates to a semiconductor component with stress-absorbing semiconductor layer (SA) and an associated fabrication method, a crystalline stress generator layer (SG) for generating a mechanical stress being formed on a carrier material (1). An insulating stress transmission layer (2), which transmits the mechanical stress which has been generated to a stress-absorbing semiconductor layer (SA), is formed at the surface of the stress generator layer (SG), with the result that in addition to improved charge carrier mobility, improved electrical properties of the semiconductor component are also obtained.

Figure 3B

